

NOT RECOMMENDED FOR NEW DESIGN USE ZXTP5240F



DSS5240T

40V PNP LOW SATURATION TRANSISTOR IN SOT23

Features

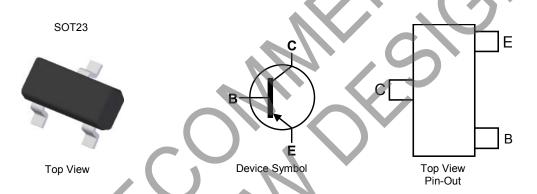
- BV_{CEO} > -40V
- I_C = -2A High Continuous Collector Current
- I_{CM} = -3A Peak Pulse Current
- Low Saturation Voltage -225mV Max @ I_C = -1A
- $R_{CE(SAT)} = 90m\Omega$ at -0.5A for a Low Equivalent On-Resistance
- 730mW Power Dissipation
- Complimentary NPN Type: DSS4240T
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ©3
- Weight 0.008 grams (Approximate)

Application

- Gate Driving MOSFETs and IGBTs
- Load Switch
- DC-DC Converters
- Battery Charging



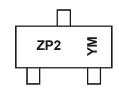
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DSS5240T-7	NRND (Use ZXTP5240F-7) (Note 5)	ZP2	7	8	3000
DSS5240T-13	NRND (Use ZXTP5240F-7) (Note 5)	ZP2	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- <1000ppm antimony compounds.</p>
 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.
- 5. NRND Not recommended for new design.

Marking Information



ZP2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	2013	2014	2015	2016	2017	2018	201	9 2	020	2021	2022	2023
Code	Α	В	С	D	Е	F	G		Н	I	J	K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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DSS5240T

Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Collector Current	I _{CM}	-3	Α
Continuous Collector Current	Ic	-2	Α
Base Current	Ι _Β	-300	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	730	mW
Power Dissipation (Note 7)	P _D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	Reja	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 7)	Reja	209	°C/W
Thermal Resistance, Junction to Lead (Note 8)	Rejl	75	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

ESD Ratings (Note 9)

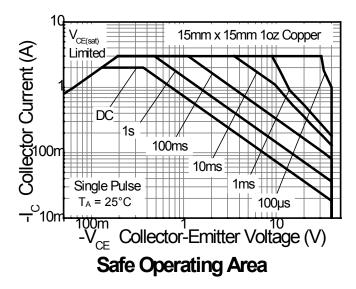
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

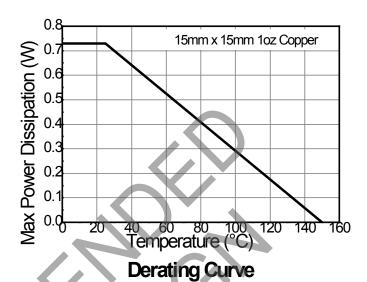
Notes:

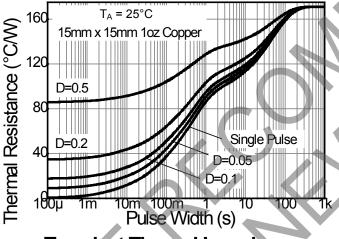
- 6. For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under To a device mounted with the collector lead on 15mm 162 copper that is on a still air conditions whilst operating in a steady-state.
 Same as Note 6, except the device is mounted on minimum recommended pad layout.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.

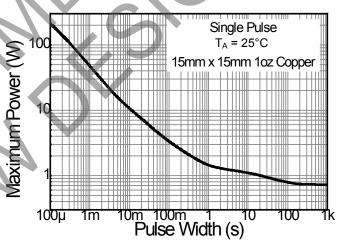


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation

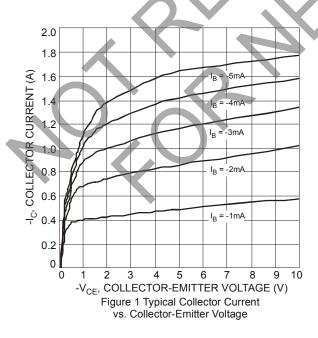


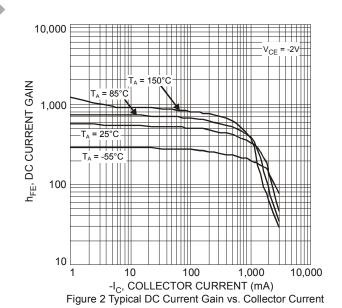
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-40	_	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-40	_	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	_	_	V	I _E = -100μA
Collector-Base Cutoff Current			_	-100	nA	$V_{CB} = -30V, I_{E} = 0$
Collector-base Cutoff Current	I _{CBO}		_	-50	μΑ	$V_{CB} = -30V$, $I_E = 0$, $T_A = +150$ °C
Emitter-Base Cutoff Current	I _{EBO}	_	_	-100	nA 🔻	$V_{EB} = -4V, I_{C} = 0$
ON CHARACTERISTICS (Note 10)						
		300	_	_		$V_{CE} = -2V$, $I_C = -0.1A$
DC Current Gain	h	260	_	_	X	V _{CE} = -2V, I _C = -0.5A
DC Current Gain	h _{FE}	210	_	_	41	V _{CE} = -2V, I _C = -1A
		100	_	_		V _{CE} = -2V, I _C = -2A
		_		-100		$I_C = -100 \text{mA}, I_B = -1 \text{mA}$
		_	-45	-110	·	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	/-,	-225	mV	$I_C = -750$ mA, $I_B = -15$ mA
				-225	- /	$I_C = -1A$, $I_B = -50mA$
				-350	_ // '	$I_C = -2A$, $I_B = -200mA$
Equivalent On-Resistance	R _{CE(SAT)}	7	90	220	mΩ	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	1	7 -	-1.1	V	I _C = -2A, I _B = -200mA
Base-Emitter Turn-on Voltage	V _{BE(ON)}	1-1	- 4	-0.75	V	V _{CE} = -2V, I _C = -100mA
SMALL SIGNAL CHARACTERISTICS					>	
Transition Frequency	f _T	100			MHz	V _{CE} = -10V, I _C = -100mA, f = 100MHz
Output Capacitance	$C_{\sf obo}$			28	pF	V _{CB} = -10V, f = 1MHz

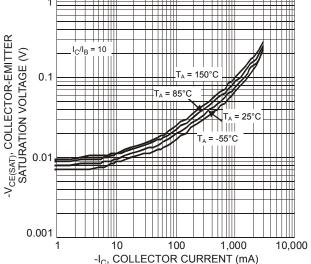
Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









-I_C, COLLECTOR CURRENT (mA)
Figure 3 Typical Collector-Emitter Saturation Voltage
vs. Collector Current

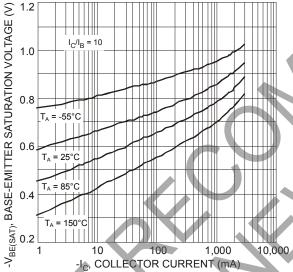


Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

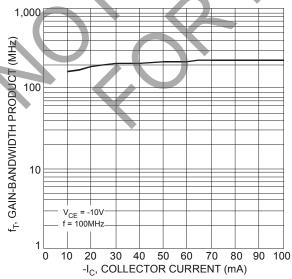
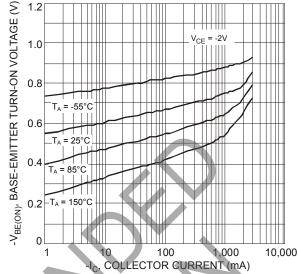


Figure 7 Typical Gain-Bandwidth Product vs. Collector Current



-I_C, COLLECTOR CURRENT (mA)
Figure 4 Typical Base-Emitter Turn-On Voltage
vs. Collector Current

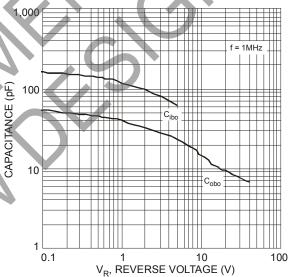


Figure 6 Typical Capacitance Characteristics

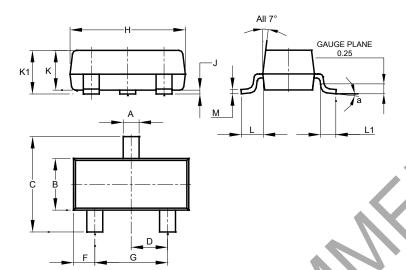


DSS5240T

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

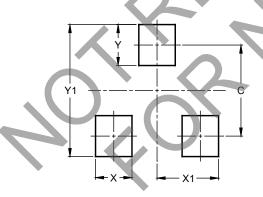


SOT23						
Dim	Min	Max	Тур			
Α_	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°	_			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
V1	29



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DSS5240T

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